



N-Channel Reduced Q_g, Fast Switching MOSFET

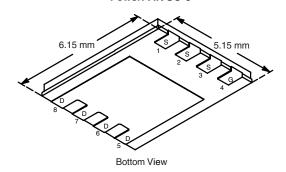
PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)			
30	0.0095 at V _{GS} = 10 V	16			
	0.0125 at V _{GS} = 4.5 V	16			

FEATURES

- Halogen-free According to IEC 61249-2-21 **Available**
- TrenchFET® Power MOSFET
- PWM Optimized for High Efficiency
- New Low Thermal Resistance PowerPAK® Package with Low 1.07 mm Profile
- 100 % R_g Tested



PowerPAK SO-8

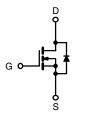


Ordering Information: Si7860ADP-T1-E3 (Lead (Pb)-free)

Si7860ADP-T1-GE3 (Lead (Pb)-free and Halogen-free)

APPLICATIONS

- **Buck Converter**
 - High Side or Low Side
- Synchronous Rectifier
 - Secondary Rectifier



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	$T_A = 25 ^{\circ}C$, unles	ss otherwise r	noted		
Parameter	Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V_{DS}	30		V
Gate-Source Voltage		V_{GS}	± 20		V
Continuous Drain Current (T _{.1} = 150 °C) ^a	T _A = 25 °C	. I _D	16	11	
Continuous Diain Current (1 j = 150 °C)	T _A = 70 °C		13	8	
Pulsed Drain Current	I _{DM}	± 50		Α	
Continuous Source Current (Diode Conduction) ^a	I _S	4.1	1.5		
Avalanche Current L = 0.1 mH		I _{AS}	35		
Single Pulse Avalanche Energy	Single Pulse Avalanche Energy		60		mJ
Maximum Dawar Dissinations	T _A = 25 °C	- P _D	4.8	1.8	W
Maximum Power Dissipation ^a	T _A = 70 °C		3.1	1.1	VV
Operating Junction and Storage Temperature Ran	T _J , T _{stg}	- 55 to 150		°C	
Soldering Recommendations (Peak Temperature)		260		C	

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Typical	Maximum	Unit		
Manifestor Investigation to Ambient (MOCETT)	t ≤ 10 s	R _{thJA}	21	26	 [
Maximum Junction-to-Ambient (MOSFET) ^a	Steady State	' 'thJA	56	70	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	1.9	2.5		

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See Solder Profile (http://www.vishay.com/ppg?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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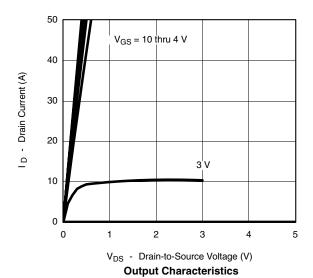
MOSFET SPECIFICATIONS	$T_{\rm J} = 25^{\circ}$	C, unless otherwise noted					
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.0		3.0	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zoro Cata Voltago Drain Current	lana	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 ^{\circ}\text{C}$			5	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	40			Α	
Durin Course On Otata Basistanas	B	$V_{GS} = 10 \text{ V}, I_D = 16 \text{ A}$		0.0079	0.0095	Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 14 \text{ A}$		0.0105	0.0125	5.2	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 16 A		60		S	
Diode Forward Voltage ^a	V_{SD}	I _S = 3 A, V _{GS} = 0 V		0.70	1.1	V	
Dynamic ^b			•	"			
Total Gate Charge	Q_g			13	18		
Gate-Source Charge	Q_{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 16 \text{ A}$		5		nC	
Gate-Drain Charge	Q_{gd}			4.0			
Gate Resistance	R_g		0.5	1.7	3.2	Ω	
Turn-On Delay Time	t _{d(on)}			18	27		
Rise Time	t _r	V_{DD} = 15 V, R_L = 15 Ω		12	18		
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ 1 A, V_{GEN} = 10 V, R_g = 6 Ω		46	70	ns	
Fall Time	t _f			19	30		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 3 A, dI/dt = 100 A/μs		40	70		

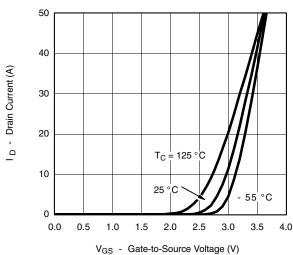
Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





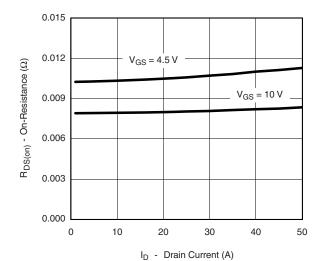
Transfer Characteristics



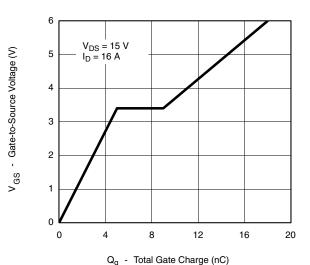




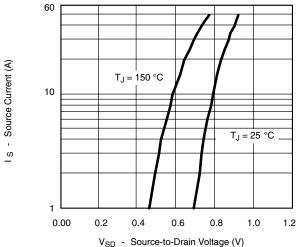
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



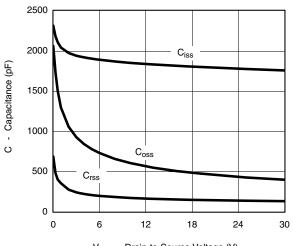
On-Resistance vs. Drain Current



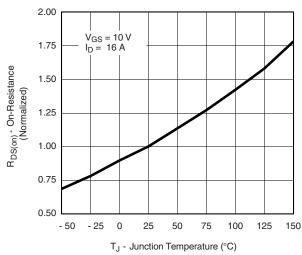
Gate Charge



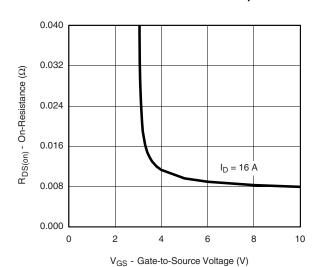
Source-Drain Diode Forward Voltage



V_{DS} - Drain-to-Source Voltage (V) **Capacitance**



On-Resistance vs. Junction Temperature

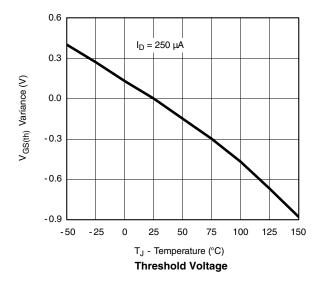


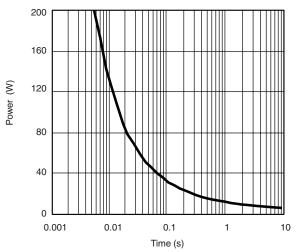
On-Resistance vs. Gate-to-Source Voltage

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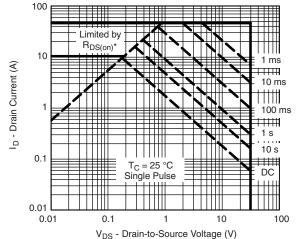
VISHAY

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



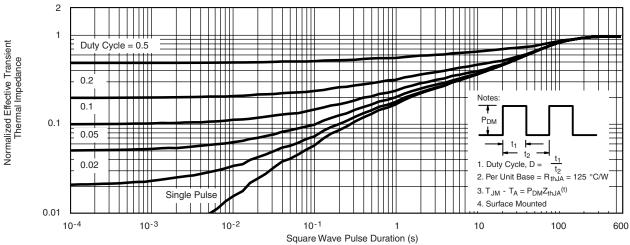


Single Pulse Power, Junction-to-Ambient



* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

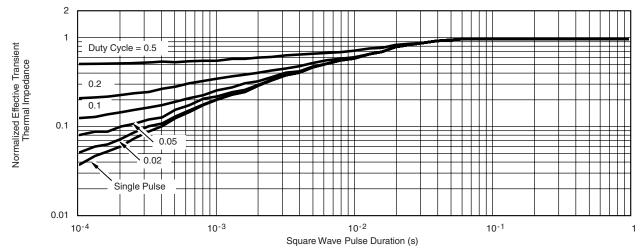
Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



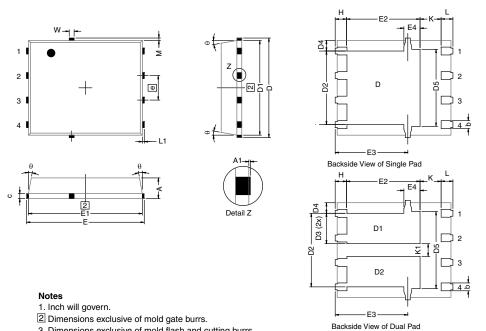
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72651.



DWG: 5881

PowerPAK® SO-8, (Single/Dual)



3. Dimensions exclusive of mold flash and cutting burrs.							
DIM.		MILLIMETERS		INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
A	0.97	1.04	1.12	0.038	0.041	0.044	
A1		-	0.05	0	-	0.002	
b	0.33	0.41	0.51	0.013	0.016	0.020	
С	0.23	0.28	0.33	0.009	0.011	0.013	
D	5.05	5.15	5.26	0.199	0.203	0.207	
	4.00	4.00	F 00	0.400	0.400	0.407	

Α	0.97	1.04	1.12	0.038	0.041	0.044	
A1		-	0.05	0	-	0.002	
b	0.33	0.41	0.51	0.013	0.016	0.020	
С	0.23	0.28	0.33	0.009	0.011	0.013	
D	5.05	5.15	5.26	0.199	0.203	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.56	3.76	3.91	0.140	0.148	0.154	
D3	1.32	1.50	1.68	0.052	0.059	0.066	
D4		0.57 typ.			0.0225 typ.		
D5		3.98 typ.		0.157 typ.			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	5.79	5.89	5.99	0.228	0.232	0.236	
E2 (for AL product)	3.30	3.48	3.66	0.130	0.137	0.144	
E2 (for other product)	3.48	3.66	3.84	0.137	0.144	0.151	
E3	3.68	3.78	3.91	0.145	0.149	0.154	
E4 (for AL product)	0.58 typ.			0.023 typ.			
E4 (for other product)		0.75 typ.			0.030 typ.		
е		1.27 BSC		0.050 BSC			
K (for AL product)		1.45 typ.		0.057 typ.			
K (for other product)		1.27 typ.		0.050 typ.			
K1	0.56	-	=	0.022	-	=	
Н	0.51	0.61	0.71	0.020	0.024	0.028	
L	0.51	0.61	0.71	0.020	0.024	0.028	
L1	0.06	0.13	0.20	0.002	0.005	0.008	
θ	0°	-	12°	0°	-	12°	
W	0.15	0.25	0.36	0.006	0.010	0.014	
M	0.125 typ.			0.005 typ.			
ECN: C13-0702-Rev. K, 20)-May-13			•			

Revison: 20-May-13 Document Number: 71655



RECOMMENDED MINIMUM PADS FOR PowerPAK® SO-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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